CORRECTION

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Correction: Epitaxial growth of β -Ga₂O₃ (–201) thin film on four-fold symmetry CeO₂ (001) substrate for heterogeneous integrations

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The authors regret the omission of the email address for the co-corresponding author, Xiaohang Li, from the original published article. Their email address is Xiaohang.li@kaust.edu.sa, and the corrected author affiliation details are shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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